

N -Channel Enhancement Mode Power MOSFET

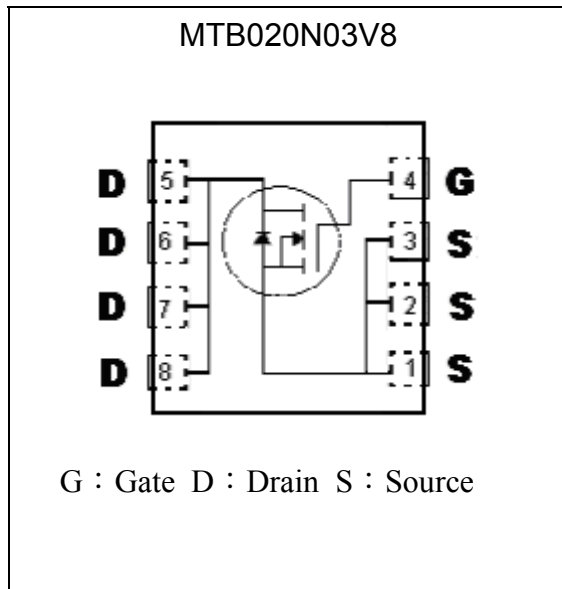
MTB020N03V8

BV_{DSS}	30V	
$I_D@V_{GS}=10V, T_A=25^\circ C$	10A	
$I_D@V_{GS}=10V, T_C=25^\circ C$	18A	
$R_{DSON(TYP)}$	$V_{GS}=10V, I_D=10A$	14.0m Ω
	$V_{GS}=4.5V, I_D=8A$	17.5m Ω

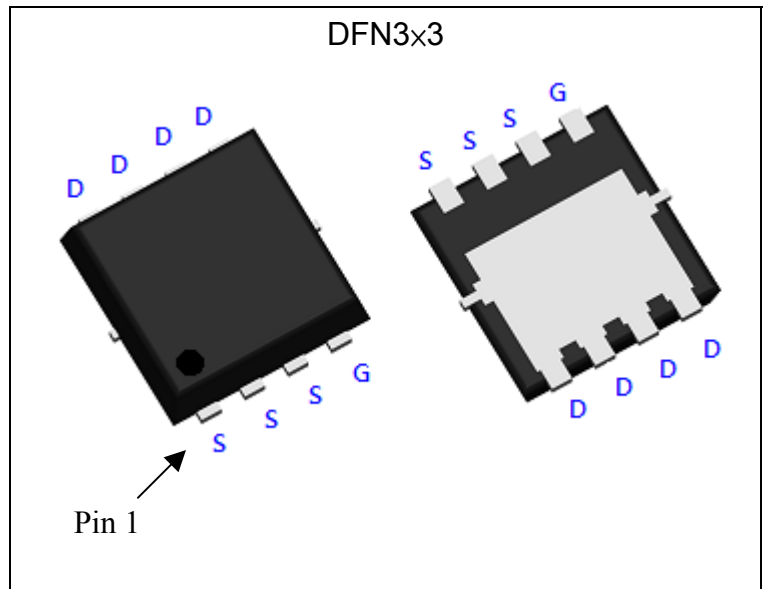
Features

- Low Gate Charge
- Simple Drive Requirement
- Pb-free lead plating package

Equivalent Circuit

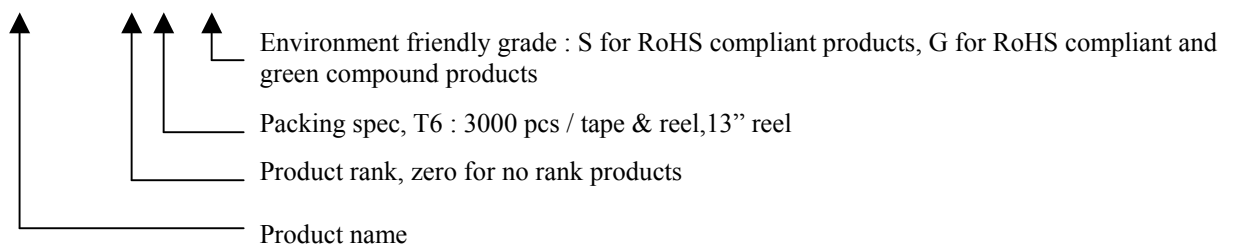


Outline



Ordering Information

Device	Package	Shipping
MTB020N03V8-0-T6-G	DFN3x3 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel





Absolute Maximum Ratings (T_C=25°C, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current @ V _{GS} =10V, T _C =25°C	I _D	18	A
Continuous Drain Current @ V _{GS} =10V, T _C =100°C		11.4	
Continuous Drain Current @ V _{GS} =10V, T _A =25°C		10	
Continuous Drain Current @ V _{GS} =10V, T _A =70°C		8	
Pulsed Drain Current *1		I _{DM}	
Single Pulse Avalanche Current	I _{AS}	18	
Single Pulse Avalanche Current @ L=0.1mH, V _{GS} =10V, V _{DD} =15V *2	E _{AS}	16.2	mJ
Total Power Dissipation @T _C =25°C	P _D	8	W
Total Power Dissipation @T _A =25°C		2.5	
Operating Junction and Storage Temperature Range	T _j , T _{stg}	-55~+150	°C

Note : *1. Pulse width limited by maximum junction temperature
 *2. 100% tested by conditions of L=0.1mH, I_{AS}=6A, V_{GS}=10V, V_{DD}=15V

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{θJC}	16	°C/W
Thermal Resistance, Junction-to-ambient, max	R _{θJA}	50 *	

* Surface mounted on a 1 in² pad of 2oz copper.

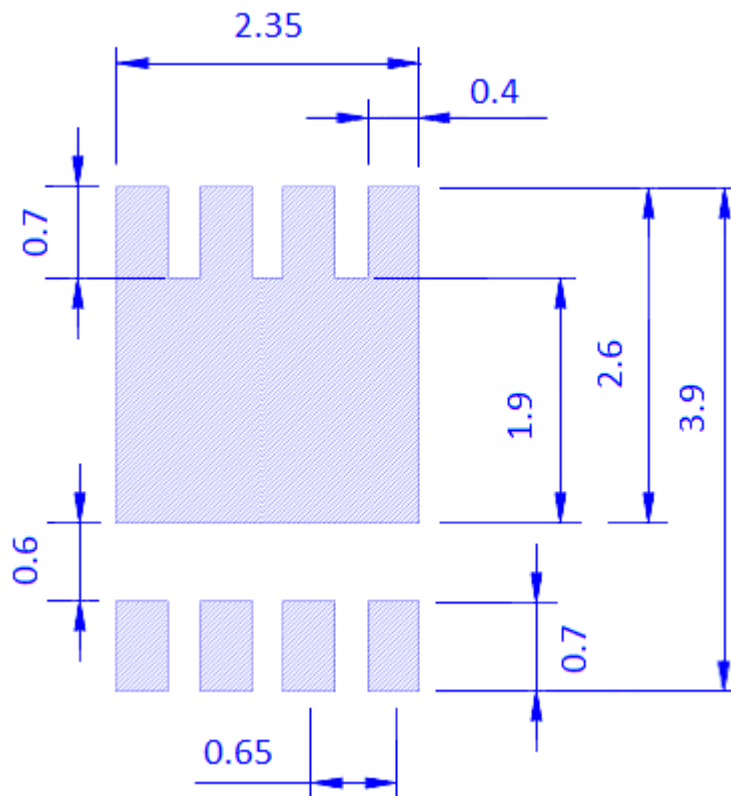
Electrical Characteristics (T_j=25°C, unless otherwise noted)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	30	-	-	V	V _{GS} =0V, I _D =250μA
ΔBV _{DSS} /ΔT _j	-	0.02	-	V/°C	Reference to 25°C, I _D =1mA
V _{GS(th)}	1	-	2.5	V	V _{DS} =V _{GS} , I _D =250μA
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	1	μA	V _{DS} =24V, V _{GS} =0V
	-	-	25		V _{DS} =24V, V _{GS} =0V, T _j =125°C
*R _{DS(ON)}	-	14	18	mΩ	I _D =10A, V _{GS} =10V
	-	17.5	25		I _D =8A, V _{GS} =4.5V
*G _{FS}	-	3.8	-	S	V _{DS} =10V, I _D =1A
Dynamic					
C _{iss}	-	492	-	pF	V _{DS} =25V, V _{GS} =0V, f=1MHz
C _{oss}	-	67	-		
C _{rss}	-	49	-		
t _{d(ON)}	-	5.8	-	ns	V _{DS} =15V, I _D =1A, V _{GS} =10V, R _G =6Ω
t _r	-	16.6	-		
t _{d(OFF)}	-	31.2	-		
t _f	-	7.6	-		

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Qg	-	12.6	-	nC	V _{DS} =15V, I _D =10A, V _{GS} =10V
Qgs	-	1.8	-		
Qgd	-	2.7	-		
Source Drain Diode					
*I _S	-	-	4	A	
*I _{SM}	-	-	16		
*V _{SD}	-	0.79	1.2	V	I _S =2.3A, V _{GS} =0V
*T _{rr}	-	7.4	-	ns	I _F =4A, V _{GS} =0V, dI _F /dt=100A/μs
Q _{rr}	-	3	-	nC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

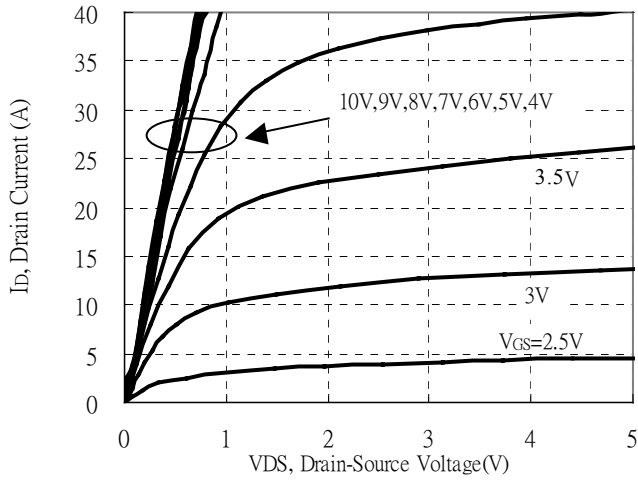
Recommended Soldering Footprint



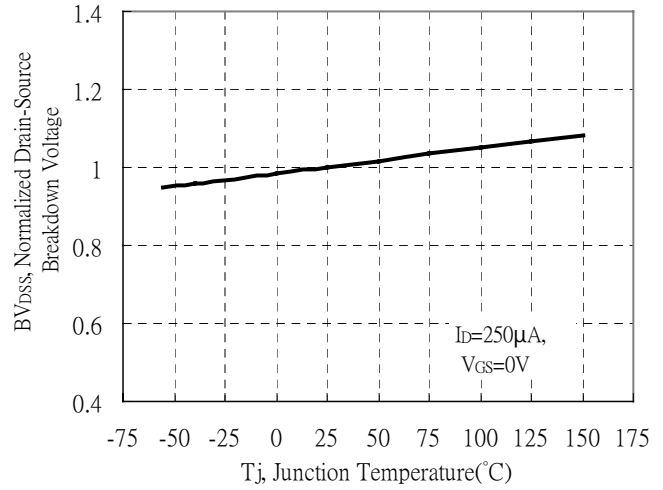
unit : mm

Typical Characteristics

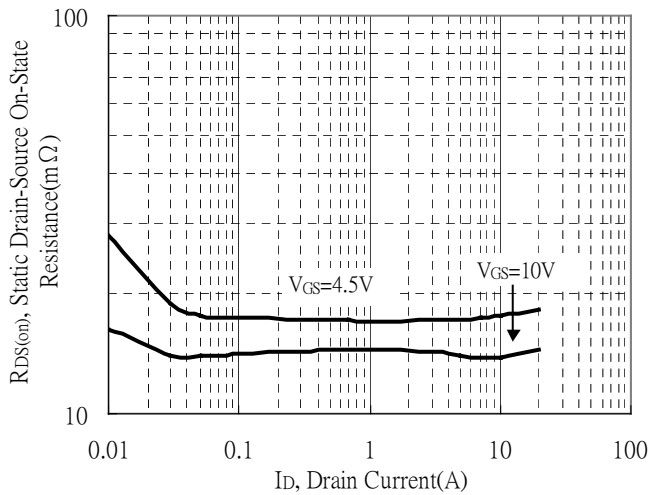
Typical Output Characteristics



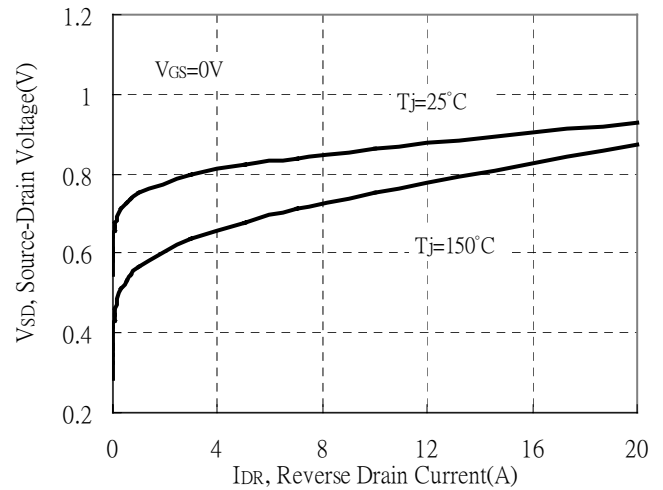
Breakdown Voltage vs Junction Temperature



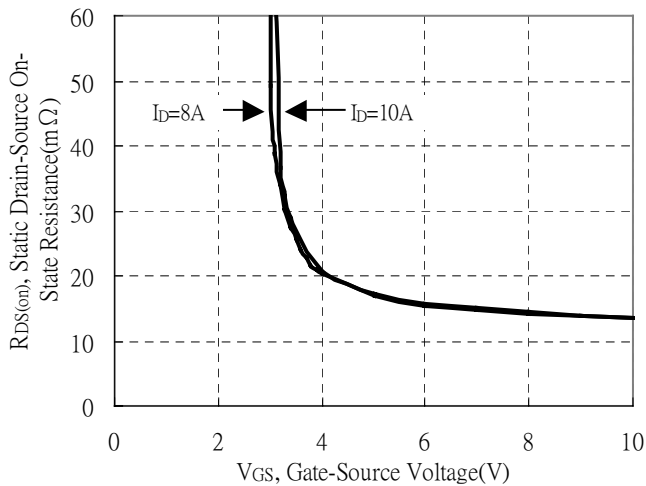
Static Drain-Source On-State resistance vs Drain Current



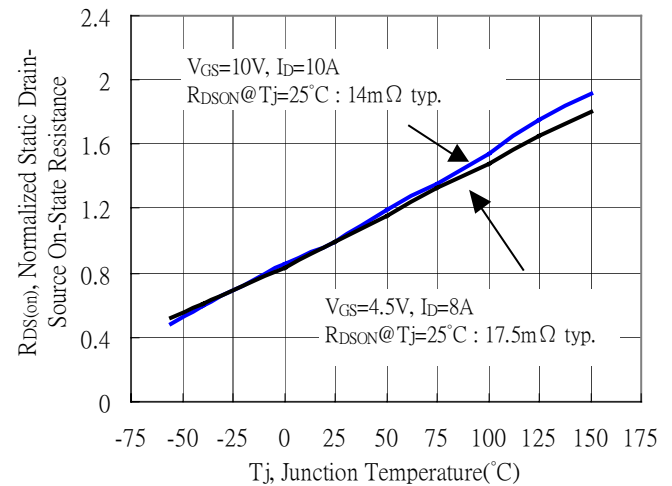
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

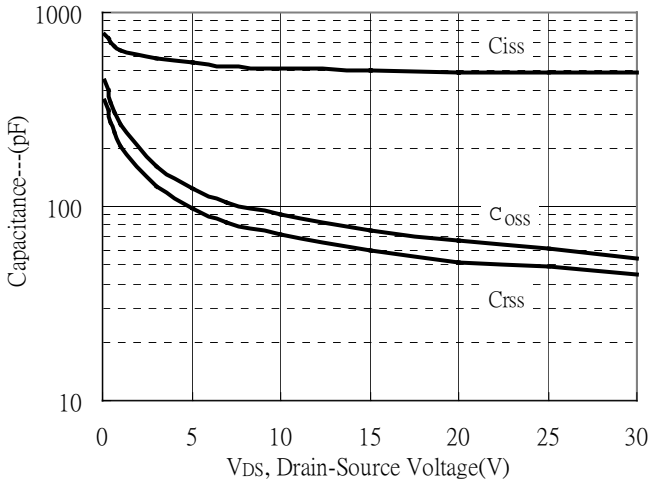


Drain-Source On-State Resistance vs Junction Temperature

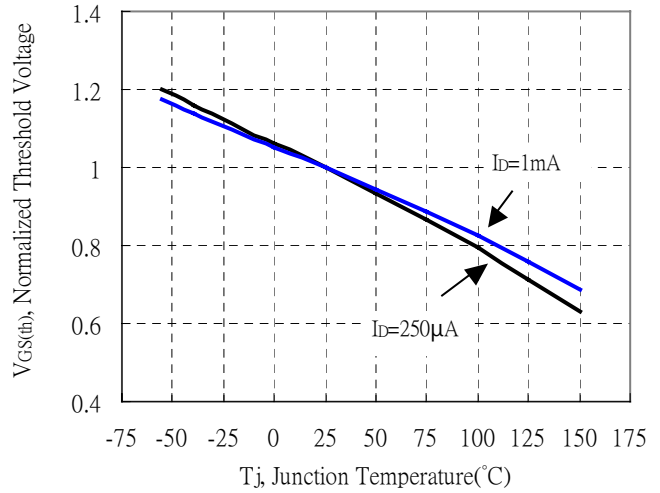


Typical Characteristics(Cont.)

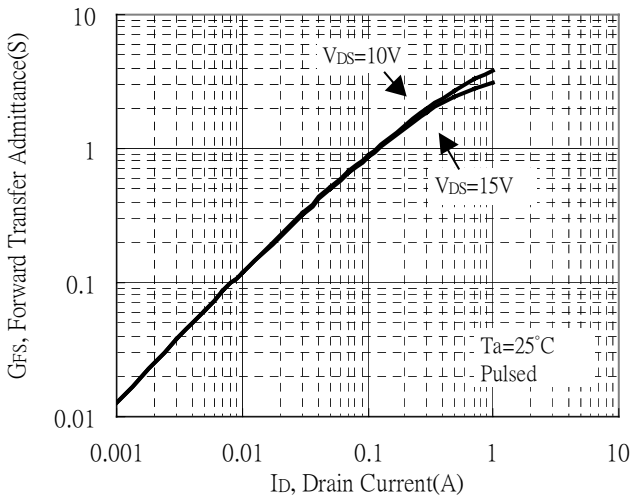
Capacitance vs Drain-to-Source Voltage



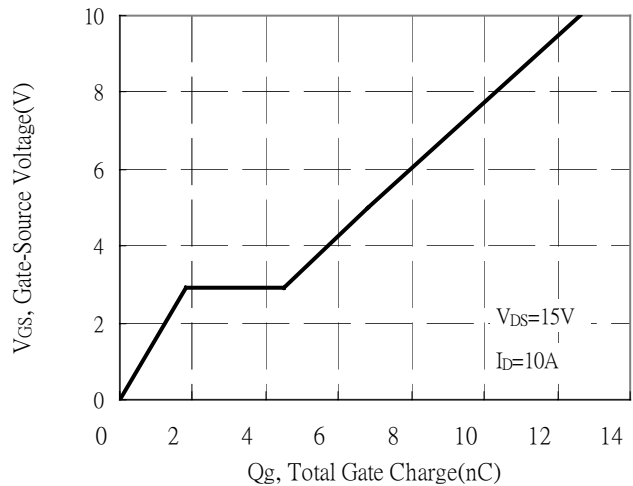
Threshold Voltage vs Junction Temperature



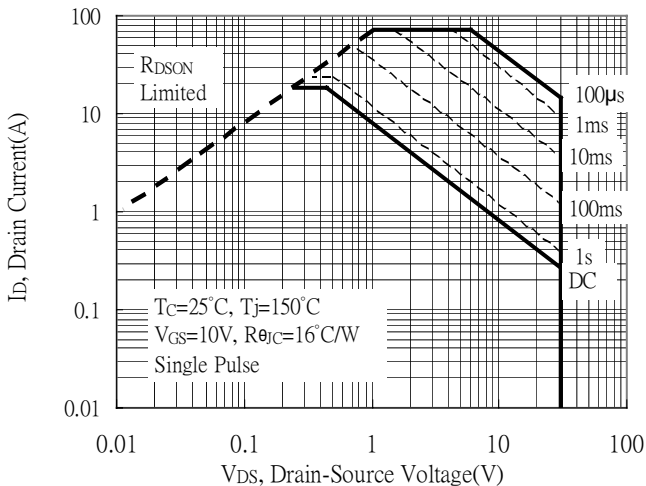
Forward Transfer Admittance vs Drain Current



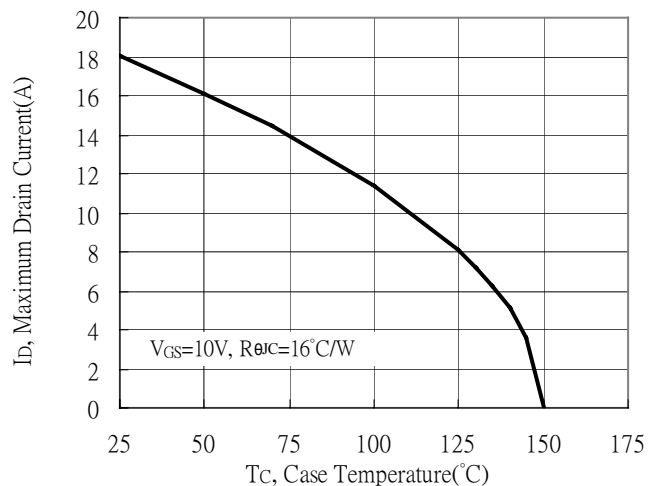
Gate Charge Characteristics



Maximum Safe Operating Area

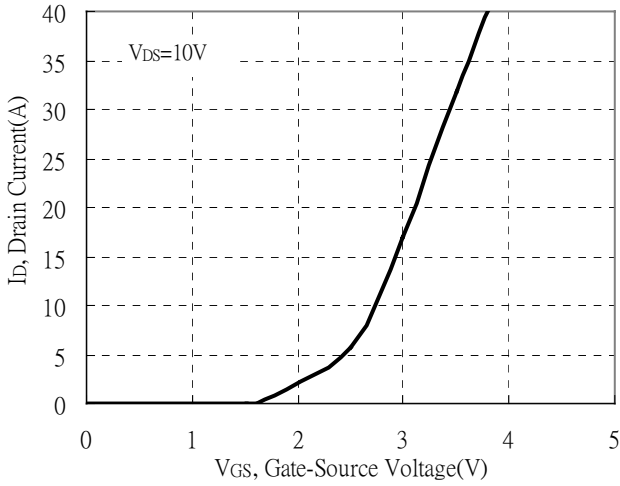


Maximum Drain Current vs Junction Temperature

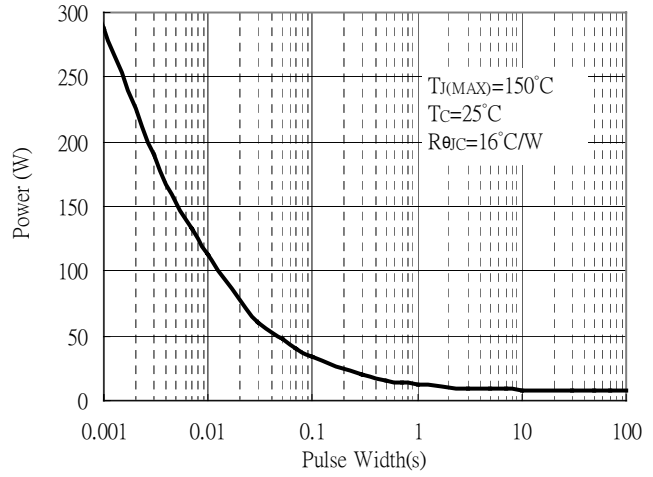


Typical Characteristics(Cont.)

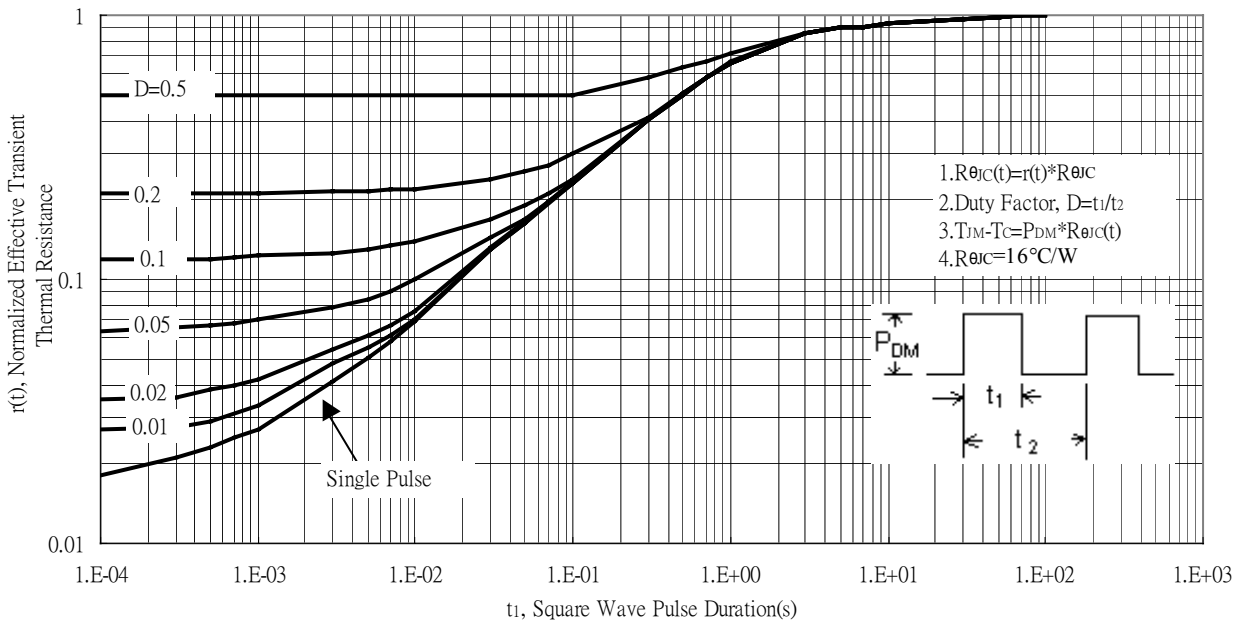
Typical Transfer Characteristics



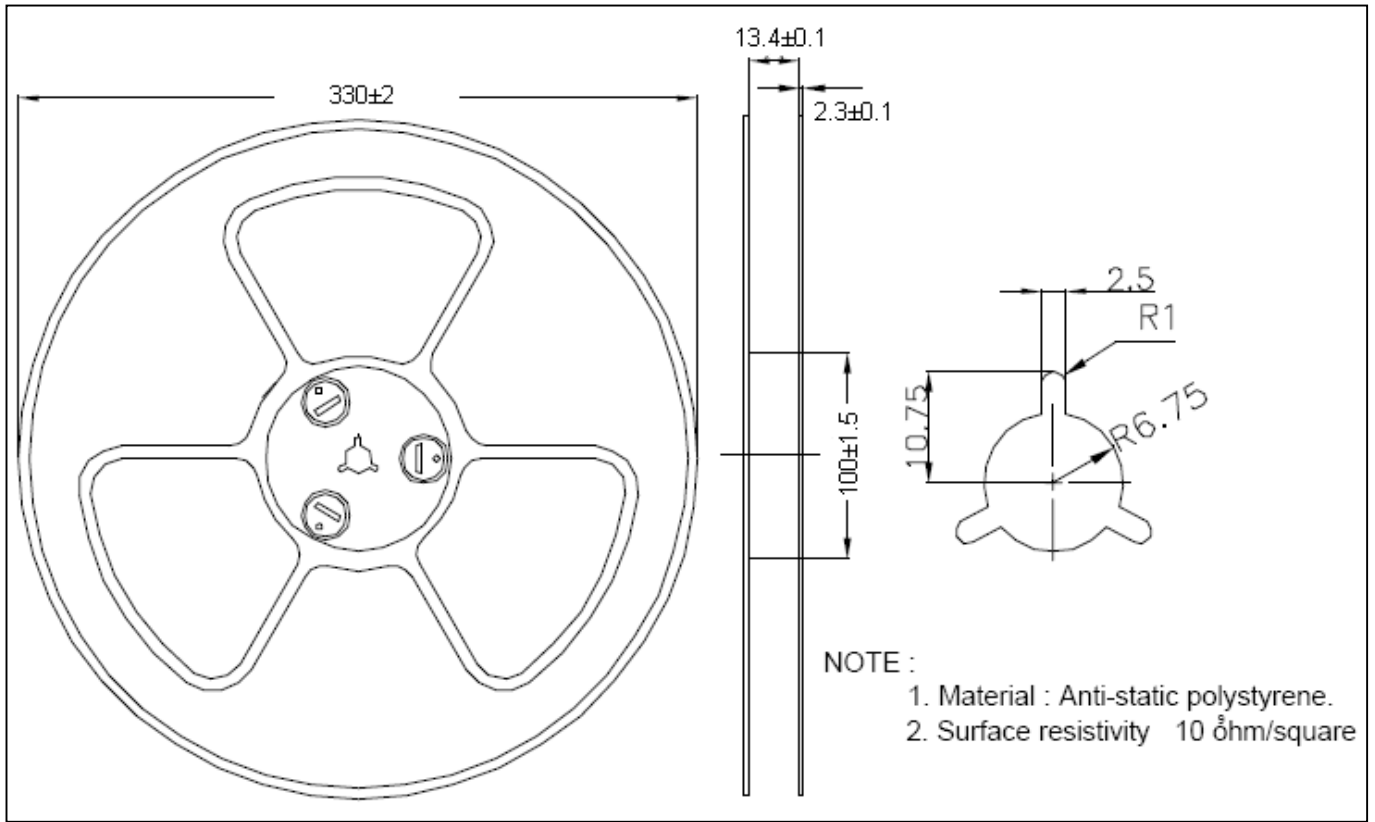
Single Pulse Power Rating, Junction to Case



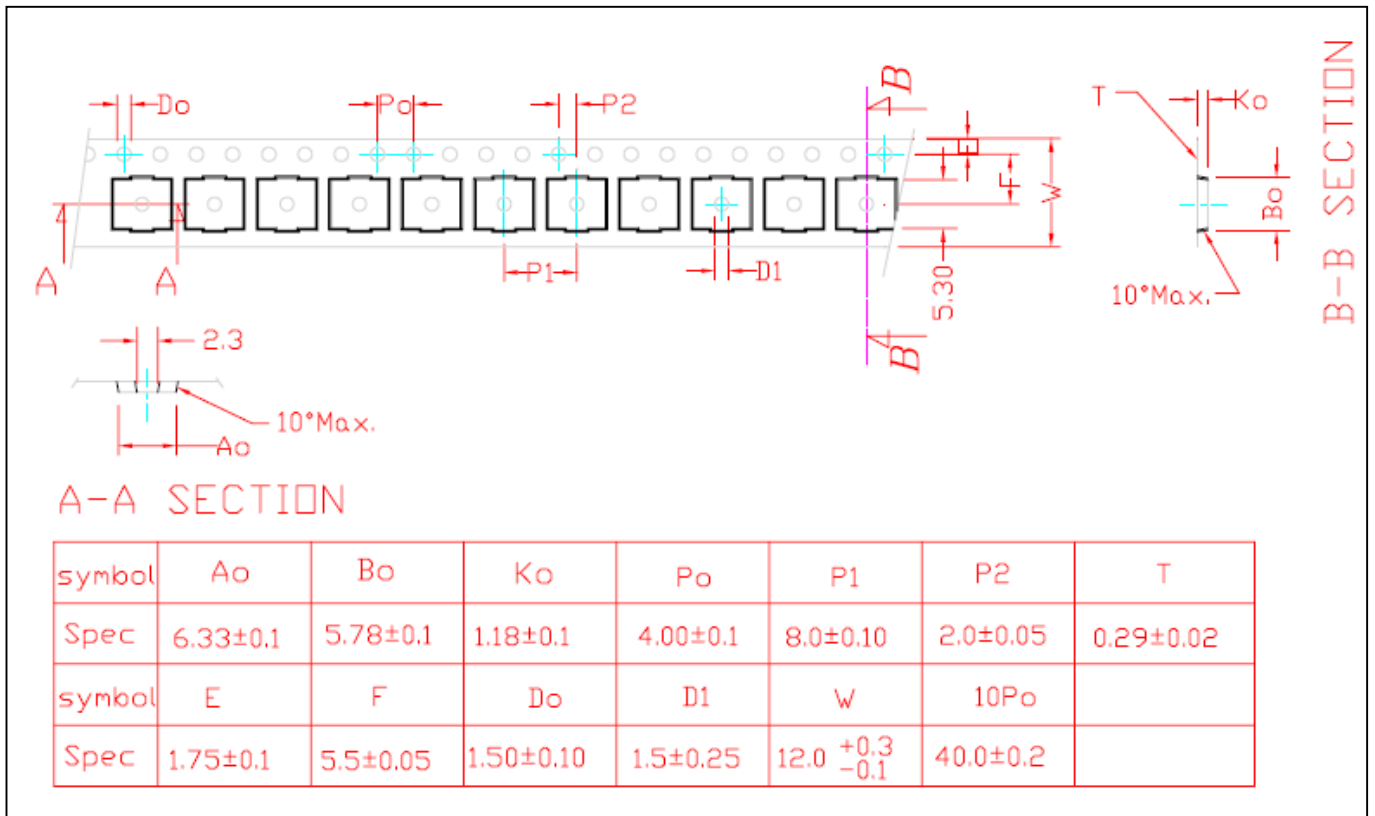
Transient Thermal Response Curves



Reel Dimension



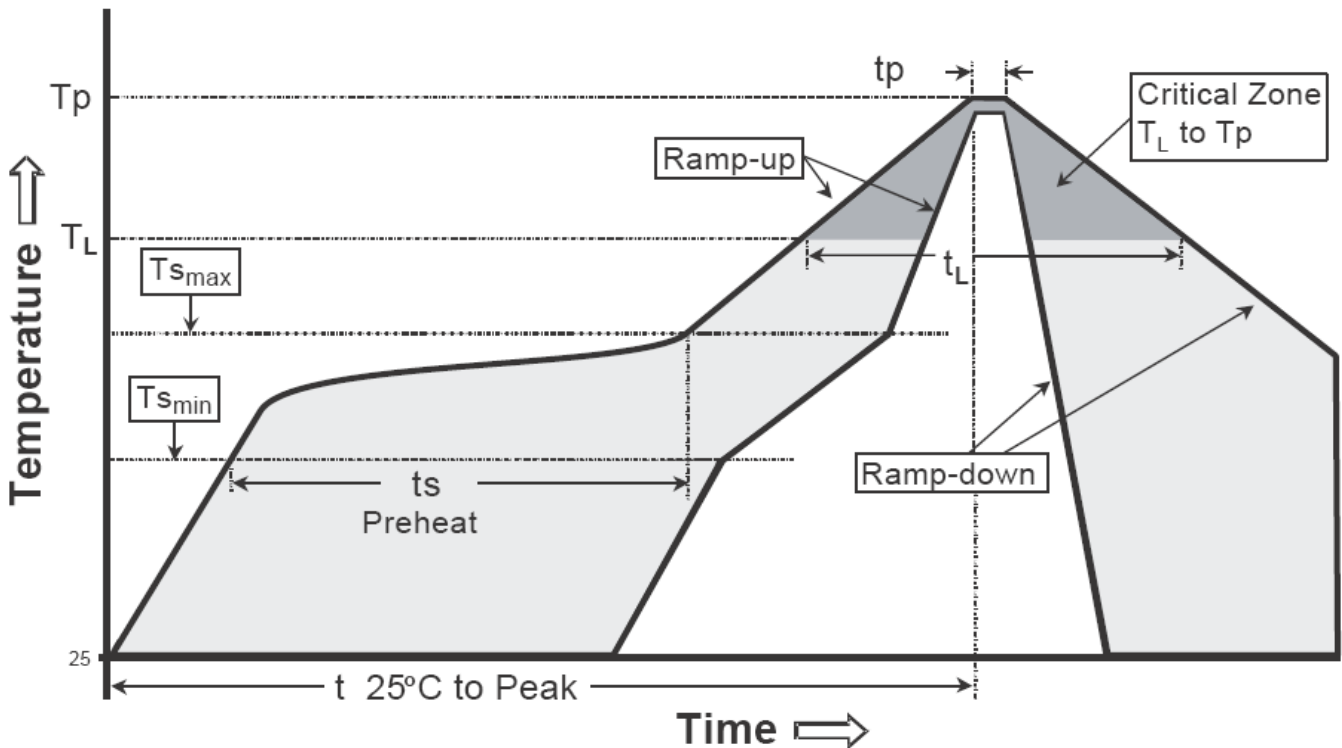
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

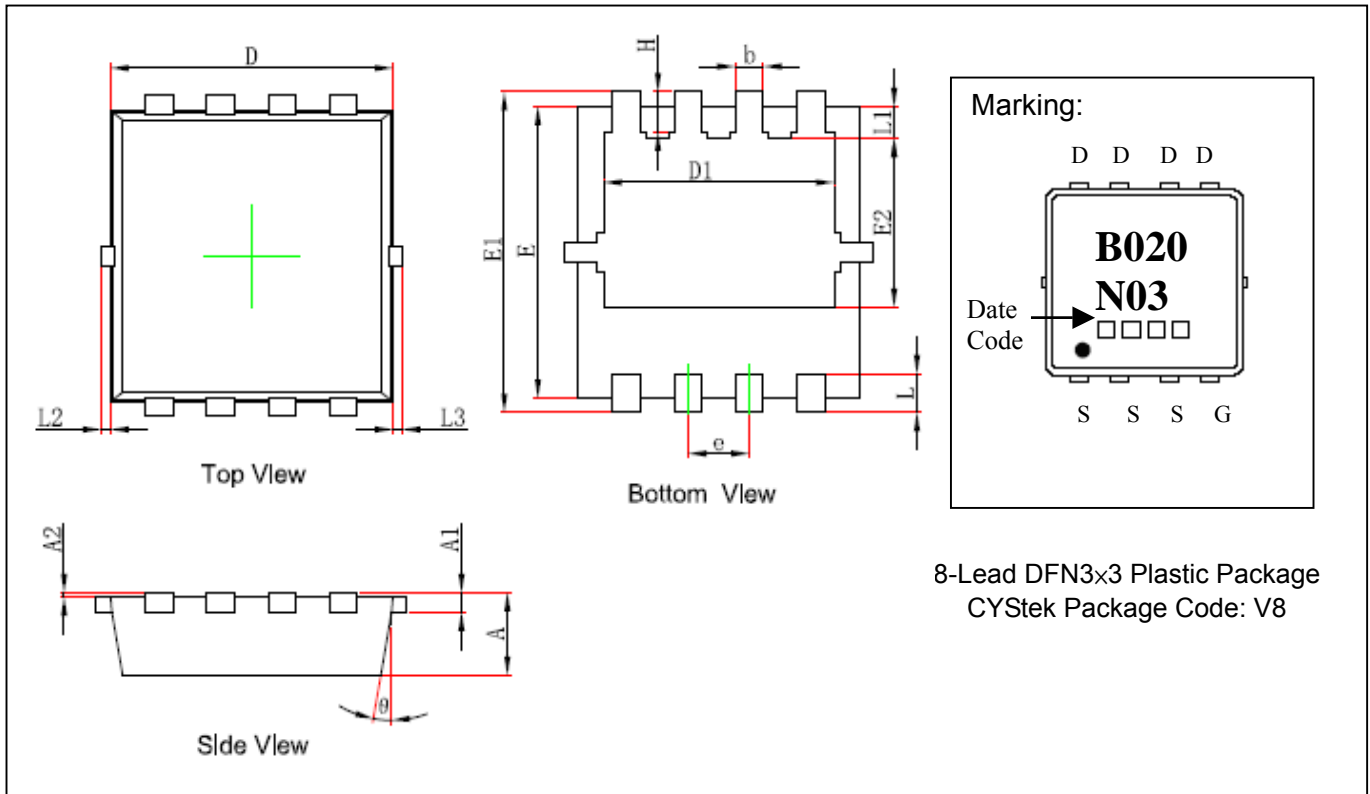
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (TL)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

DFN3x3 Dimension



*: Typical

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.605	0.850	0.026	0.033	b	0.200	0.400	0.008	0.016
A1	0.152	REF	0.006	REF	e	0.550	0.750	0.022	0.030
A2	0.000	0.050	0.000	0.002	L	0.300	0.500	0.012	0.020
D	2.900	3.100	0.114	0.122	L1	0.180	0.480	0.007	0.019
D1	2.300	2.600	0.091	0.102	L2	0.000	0.100	0.000	0.004
E	2.900	3.100	0.114	0.122	L3	0.000	0.100	0.000	0.004
E1	3.150	3.450	0.124	0.136	H	0.315	0.515	0.012	0.020
E2	1.535	1.935	0.060	0.076	θ	9°	13°	9°	13°

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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